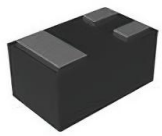
SI3134KL3-TP Datasheet



DiGi Electronics Part Number	SI3134KL3-TP-DG
Manufacturer	Micro Commercial Co
Manufacturer Product Number	SI3134KL3-TP
Description	MOSFET N-CH 20V 750MA DFN1006-3
Detailed Description	N-Channel 20 V 750mA (Ta) 100mW Surface Mount DFN1006-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SI3134KL3-TP	Micro Commercial Co
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	750mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.8V, 4.5V	500mOhm @ 150mA, 4.5V
Vgs(th) (Max) @ Id:	Vgs (Max):
1.1V @ 250µA	±12V
Input Capacitance (Ciss) (Max) @ Vds:	FET Feature:
120 pF @ 16 V	-
Power Dissipation (Max):	Operating Temperature:
100mW	-55°C ~ 150°C (TJ)
Mounting Type:	Supplier Device Package:
Surface Mount	DFN1006-3
Package / Case:	Base Product Number:
SC-101, SOT-883	SI3134

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

Micro Commercial Components

SI3134KL3

Features

- Operated at Low Logic Level Gate Drive
- N-Channel Switch with Low $R_{DS(on)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- ESD Human Body Model 1400V
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-Channel MOSFET

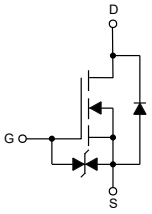
Maximum Ratings

- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Maximum Thermal Resistance: 1250°C/W Junction to Ambient

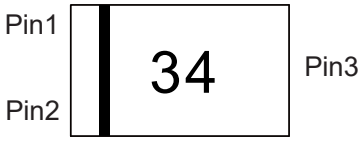
Parameter	Symbol	Rating	Unit
Drain -source Voltage	V_{DS}	20V	V
Gate -Source Voltage	V_{GS}	±12	V
Drain Current-Continuous(2)	I_D	0.75	A
Pulsed Drain Current	I_{DM}	1.8	A
Power Dissipation(3)	P_D	0.1	W

Note: 1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

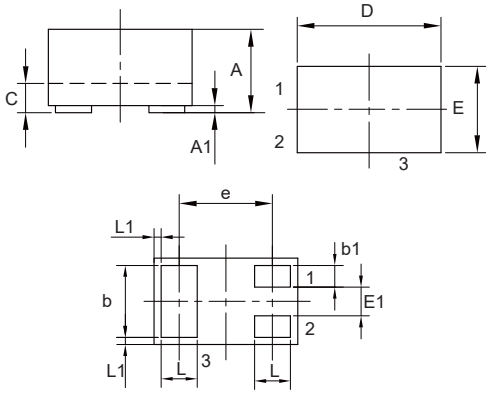
Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN

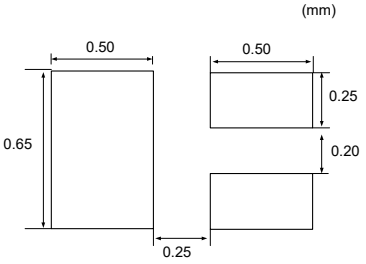


DFN1006-3



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.018	0.022	0.45	0.55	
A1	0.000	0.002	0.00	0.05	
b	0.018	0.022	0.45	0.55	
b1	0.004	0.008	0.10	0.20	
c	0.005	0.007	0.12	0.18	
D	0.037	0.042	0.95	1.075	
E	0.022	0.026	0.55	0.675	
E1	0.006	0.010	0.15	0.25	
e	0.026		0.65		TYP.
L	0.008	0.012	0.20	0.30	
L1	0.0002		0.05		TYP.

Suggested Solder Pad Layout



ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	20			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	0.35	0.75	1.1	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =20V, V_{GS} =0V			1.0	μA
Gate-body Leakage Current	I_{GSS}	V_{GS} =± 10V, V_{DS} =0V			±20	μA
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=4.5V, I_D=150mA		0.25	0.5	Ω
		V_{GS}=2.5V, I_D=150mA		0.30	0.7	
		V_{GS}=1.8V, I_D=150mA		0.37	0.9	
Forward transconductance	g_{FS}	V_{DS}=10V, I_D=150mA	150			mS
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=150mA			1.2	V
Dynamic Characteristics						
Input Capacitance(4)	C_{iss}	V_{DS}=16V,V_{GS}=0V, f=1MHz		79	120	pF
Output Capacitance(4)	C_{oss}			13	20	
Reverse Transfer Capacitance(4)	C_{rss}			9	15	
Switching Characteristics						
Turn-on Delay Time(5)	$t_{d(on)}$	V_{DS}=10V,V_{GS}=4.5V,I_D=500 mA, R_{GEN}=10Ω		6.7		ns
Turn-off Delay Time(5)	$t_{d(off)}$			17.3		
Rise Time(5)	t_r			4.8		
Fall Time(5)	t_f			7.4		

Note:

2. Surface Mounted on FR4 board using the minimum recommended pad size.

3. Pulse Test: Pulse width ≤300μs,duty cycle≤2%.

4. Graranteed by design, not subject to productin

5. Switching characteristics are independent of operating junction temperatures.

Curve Characteristics

Fig. 1 - Output Characteristics

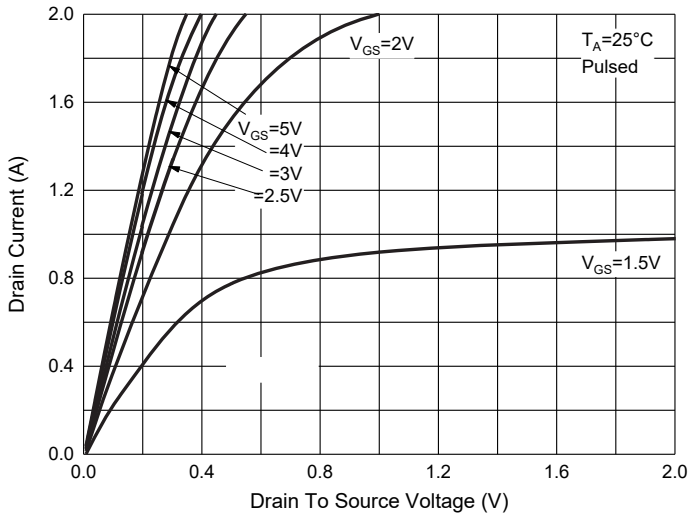


Fig. 2 - Transfer Characteristics

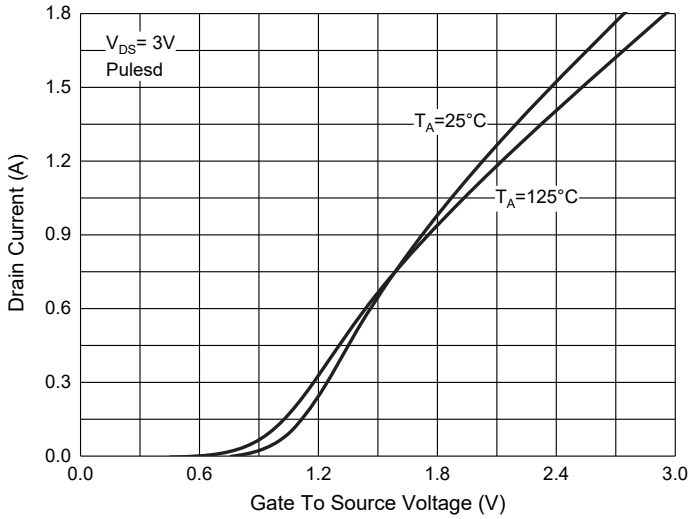


Fig. 3 - $R_{DS(ON)}$—I_D

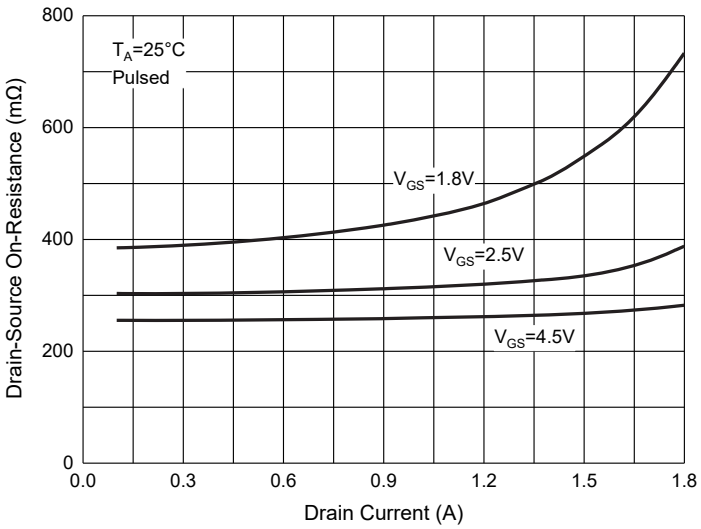


Fig. 4- $R_{DS(ON)}$—V_{GS}

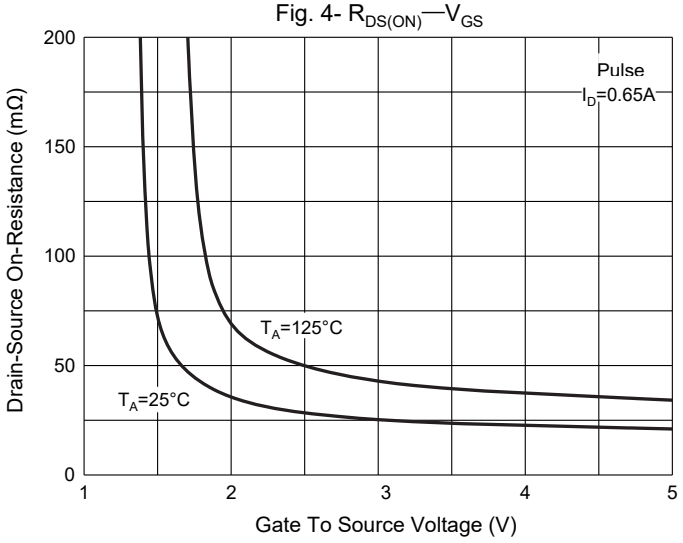


Fig. 5 - I_S—V_{SD}

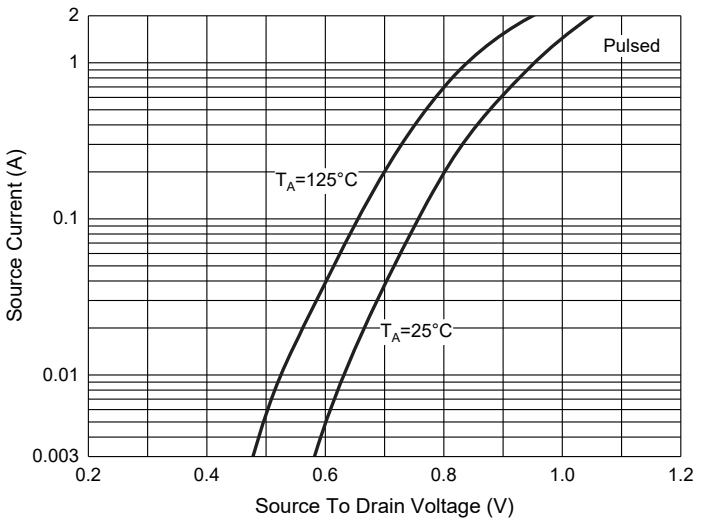
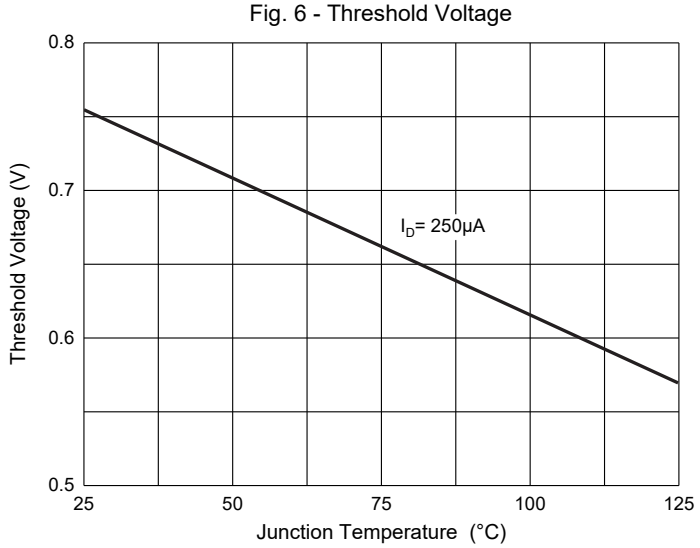


Fig. 6 - Threshold Voltage



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:10Kpcs/Reel

OUR CERTIFICATE

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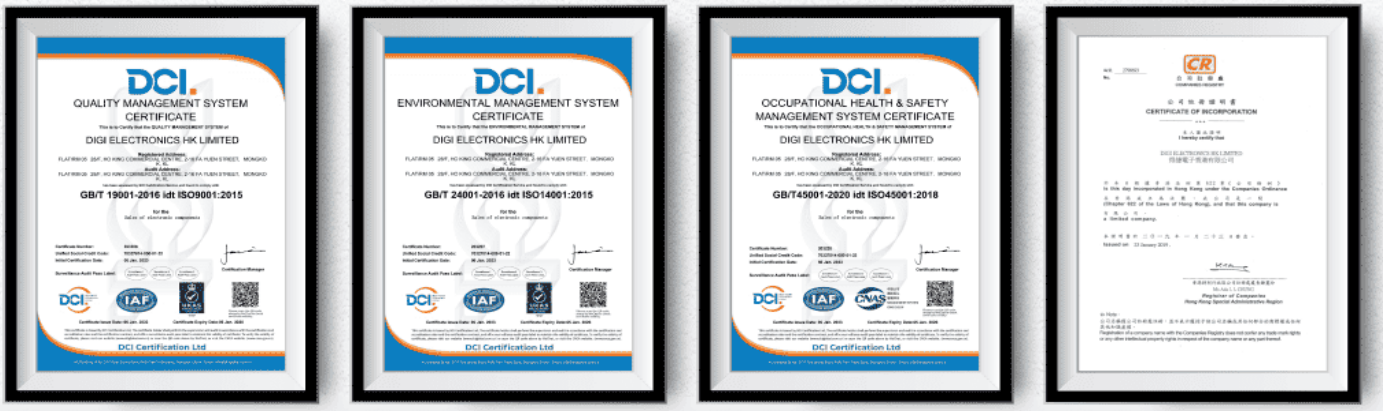

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